Rehm

CUSTOMER		NO. MMST8098		
SUBJECT		PAGE 1 of 2		
SOT-23 TRANSISTOR, NPN , SILICON		DATE January 14, 1987		
ABSOLUTE MAXIMUM RATINGS: (Ta = 25°C)				
Collector-Base Voltage	Vсво	60 V		
Collector-Emitter Voltage	VCEO	60 V		
Emitter-Base Voltage	VEBO	6 γ		
Collector Current	I _C	200 mA		
Power Dissipation-Free Air	Р _D	200 mW		
Power Dissipation-Ceramic Substrate	Р _D	350 mW		
Operating and Storage Junction Temperatu	re T _J , T _{stg}	-55 to 150 °C		
Solder Temperature (10 seconds)		260 °C		
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THE JAPAN	IESE STYLE SC-5	59 PACKAGE		
MARKING:	<u>de</u> M/ 8n 8n 8n	NG: JLK, 500 per BAG AGAZINES OF 50 EACH nm T&R, T-146 3K/REEL nm T&R, T-147 3K/REEL nm T&R, T-246 10K/REEL nm T&R, T-247 10K/REEL		
EEMARKS: PROCESS: <u>C-22</u> Thermal R	Resistance R _{OJA}	$\frac{625}{\text{FREE AIR, TA}} = 25^{\circ}\text{C}$		
ROHM ELECTRONICS 3034 Owen Drive, Antioch, TN 37013 TEL/GENERAL 2009 EAX/GENERAL 2022	APPROVAL	CHECK DESIG		
TEL:(615)641-2020 FAX:(615)641-2022				

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CUSTOMER		NO. MMST8098				
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SUBJECT TRANSISTOR, NPN ,SILICON S0T-23			DATE January 14, 1987			
ELECTRICA	L CHARACTERISTICS: (Ta = 25°C Unless	s Otherwi	se Specified)		
PARAMETER	TEST CONDITIONS	MIN	TYP	MAX	UNIT	
BV _{CBO}	I _C = 100 μA	60			V	
BVCEO	I _C = 10 mA	60			- V	
BV _{EBO}	I _E = 10 μA	6			V	
I _{CBO}	V _{CB} = 60 V		2.0	100	nA	
I _{CEO}	V _{CE} = 60 V		1.5	100	nA	
I _{EBO}	V _{EB} = 6 V		1.0	100	'nA	
hFE	$I_{C} = 1.0 \text{ mA}, V_{CE} = 5.0 \text{ V}$	100		300		
hfe	$I_{C} = 10 \text{ mA}, V_{CE} = 5.0 \text{ V}$	100				
hfe	$I_{C} = 100 \text{ mA}, V_{CE} = 5.0 \text{ V}$	75				
V _{CE} (SAT)	$I_{C} = 100 \text{ mA}, I_{B} = 5.0 \text{ mA}$			0.4	V	
V _{CE} (SAT)	$I_{C} = 100 \text{ mA}, I_{B} = 10 \text{ mA}$			0.3	V	
V _{BE} (ON)	$I_{C} = 1.0 \text{ mA}, V_{CE} = 5.0 \text{ V}$	0.5		0.7	V	
fŢ	$I_{C} = .10 \text{ mA}, V_{CE} = 5.0 \text{ V}, \text{ f} = 100 \text{MHz}$	150	350		MHz	
Cob	$V_{CB} = 5.0 V$, $I_E = 0$, $f = 1.0 MHz$			6.0	pF	
C _{ib}	$V_{BE} = 5.0 V$, $I_{C} = 0$, $f = 1.0 MHz$			25	pF	
ROHM ELECTRONICS 3034 Owen Drive, Antioch, TN 37013		APPRO	1	IECK	DESIGN	
TEL:(615)641-2020	FAX:(615)641-2022	ERE) 1º1				
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